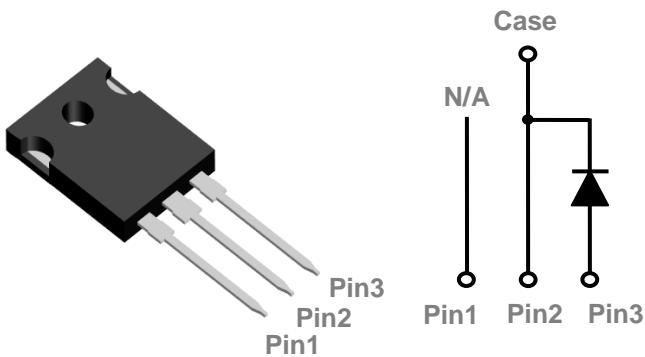


General Description

These 650V high performance series of SiC schottky diodes are using the most advanced technology to suit for high frequency and high efficiency power systems with extreme low reverse recovery charge and can be stand up to 175°C maximum junction temperature.

TO247-3L Pin Configuration



V_{BR}	I_F ($T_C = 140^\circ C$)	Q_C
650V	20A	50nC

Features

- 650V, 20A, 175°C junction temperature
- Extremely fast switching
- Zero Reverse Recovery Current
- Positive temperature coefficient
- Green device available

Applications

- Switching mode power supplies
- Motor drives
- Power Converters
- PFC, Power factor correction

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_R	DC Peak Reverse Voltage, $T_j=25^\circ C$	650	V
V_{RRM}	Repetitive Peak Reverse Voltage, $T_j=25^\circ C$	650	V
V_{RSM}	Surge Peak Reverse Voltage, $T_j=25^\circ C$	650	V
I_F	Continuous Forward Current, $T_c=25^\circ C$	54	A
	Continuous Forward Current, $T_c=140^\circ C$	20	A
I_{FSM}	Non-Repetitive Forward Surge current $T_c = 25^\circ C$, $T_p=10\text{ms}$ Half Sine Pulse	80	A
T_J	Maximum operating Junction Temperature Range	175	°C
T_{STG}	Storage Temperature Range	-55 to 175	°C

Thermal Characteristics

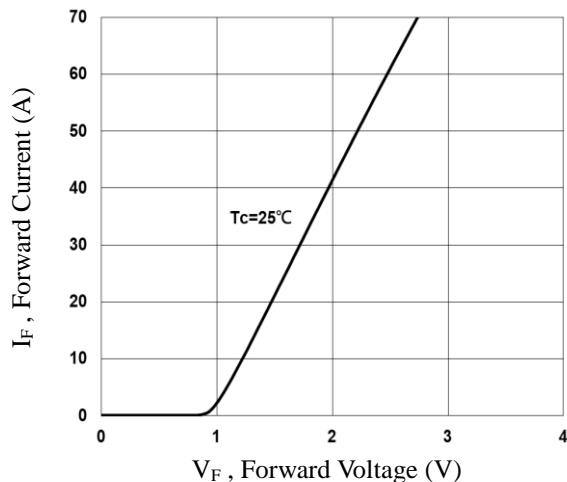
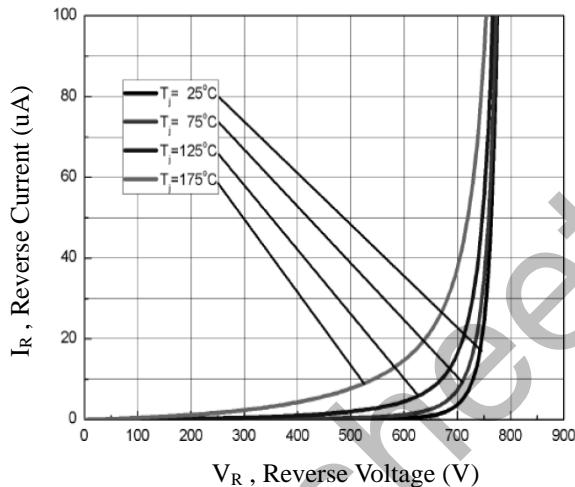
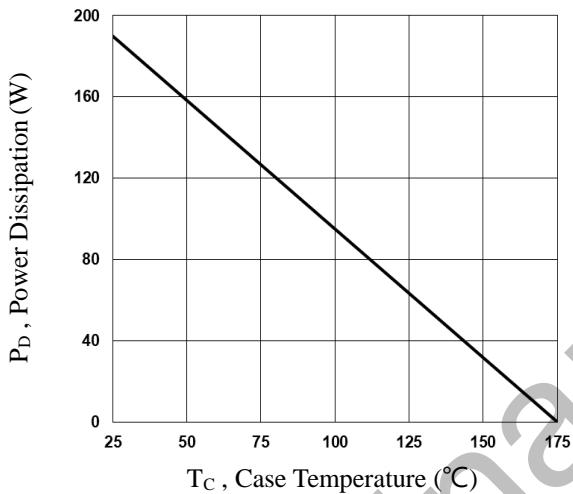
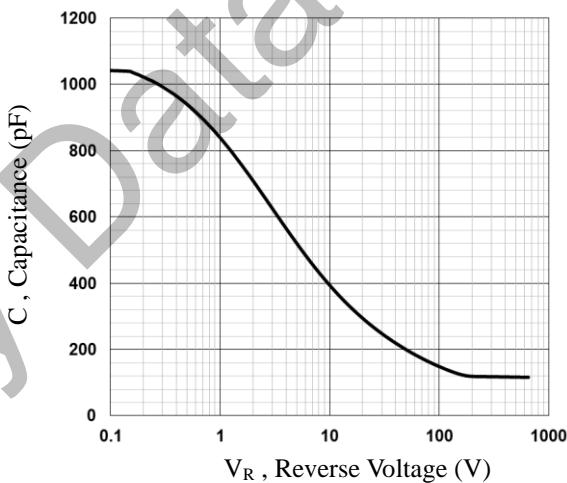
Symbol	Parameter	Typ.	Max.	Unit
R_{eJC}	Thermal Resistance Junction to Case	---	0.8	°C /W



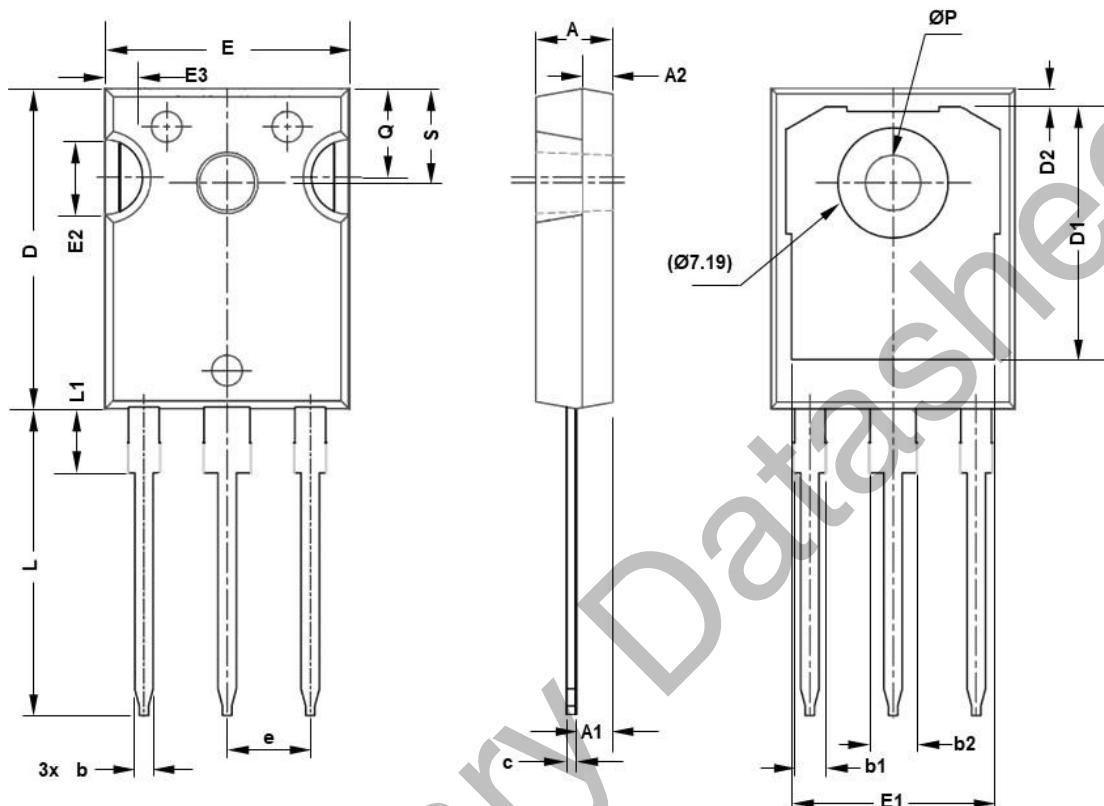
20A 650V Silicon Carbide Schottky Diode

PCX20S65Z**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
VDC	DC Blocking Voltage	$I_R=100\mu\text{A}$, $T_J=25^\circ\text{C}$	650			V
V_F	Forward Voltage	$I_F=20\text{A}$, $T_J=25^\circ\text{C}$	---	1.5	1.8	V
		$I_F=20\text{A}$, $T_J=140^\circ\text{C}$	---	2.1	2.6	V
I_R	Reverse Current	$V_R=650\text{V}$, $T_J=25^\circ\text{C}$	---	---	100	μA
		$V_R=650\text{V}$, $T_J=175^\circ\text{C}$	---	---	250	μA
Q_C	Total Capacitive Charge	$V_R=400\text{V}$, $I_F=20\text{A}$ $dI/dt=300\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	50	---	nC
C	Total Capacitance	$V_R=10\text{V}$, $f=1\text{MHz}$	---	400	---	pF
		$V_R=300\text{V}$, $f=1\text{MHz}$	---	120	---	
		$V_R=600\text{V}$, $f=1\text{MHz}$	---	118	---	


Fig.1 Forward Characteristics

Fig.2 Reverse Characteristics

Fig.3 Power Dissipation

Fig.4 Capacitance Characteristics

TO247 PACKAGE INFORMATION



SYMBOL	mm		SYMBOL	mm	
	MIN	MAX		MIN	MAX
A	4.83	5.21	E2	4.32	5.49
A1	2.29	2.55	E3	2.15	2.80
A2	1.50	2.49	e	5.44BSC	
b	1.12	1.33	L	19.81	20.32
b1	1.91	2.39	L1	4.10	4.40
b2	2.87	3.22	ØP	3.56	3.65
C	0.55	0.69	Q	5.39	6.20
D	20.80	21.10	S	6.04	6.30
D1	16.25	17.65			
D2	0.51	1.35			
E	15.75	16.13			
E1	13.46	14.16			